



CREST



JST/CREST/2D Workshop in Kobe

March 16th on Friday, 2018,

Room E (Valencia), Ariston Hotel Kobe/The Kobe Chamber of Commerce and Industry

- 13:58 Welcome address, Atsushi Kurobe, JST/Toshiba
- 14:00 “Two-Dimensional Materials for Next-Generation Electronics,”
Kaustav Banerjee, UC Santa Barbara
- 14:30 “Graphene/h-BN van der Waals superlattices for functional devices,”
Tomoki Machida, University of Tokyo
- 15:00 “Synthesis and Application of Graphene and Graphene Nanoribbons,”
Shintaro Sato, Fujitsu Limited, Fujitsu Labs Ltd.
- 15:30 Break
- 15:40 “Process and Device Technologies on Sputter-Deposited MoS₂ Film,”
Hitoshi Wakabayashi, Tokyo Institute of Technology
- 15:55 “Two-Dimensional Self-Assembled Monolayer Gate Dielectric for Interface Engineering in MoS₂ FET,” Takamasa Kawanago, Tokyo Institute of Technology
- 16:10 “On-Surface Synthesis of Graphene Nanoribbon with Carbon-Fluorine Bond Cleavage,”
Hironobu Hayashi, NAIST
- 16:25 “Electric field effect in graphene/TMD heterostructures,” Rai Moriya, University of Tokyo
- 16:40 “Fabrication techniques for various TMDC materials and their high quality thin films with organic precursors,” Yusuke Hibino, Meiji University
- 16:55 Closing remarks,, Shintaro Sato, Fujitsu Limited, Fujitsu Labs Ltd.

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